

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

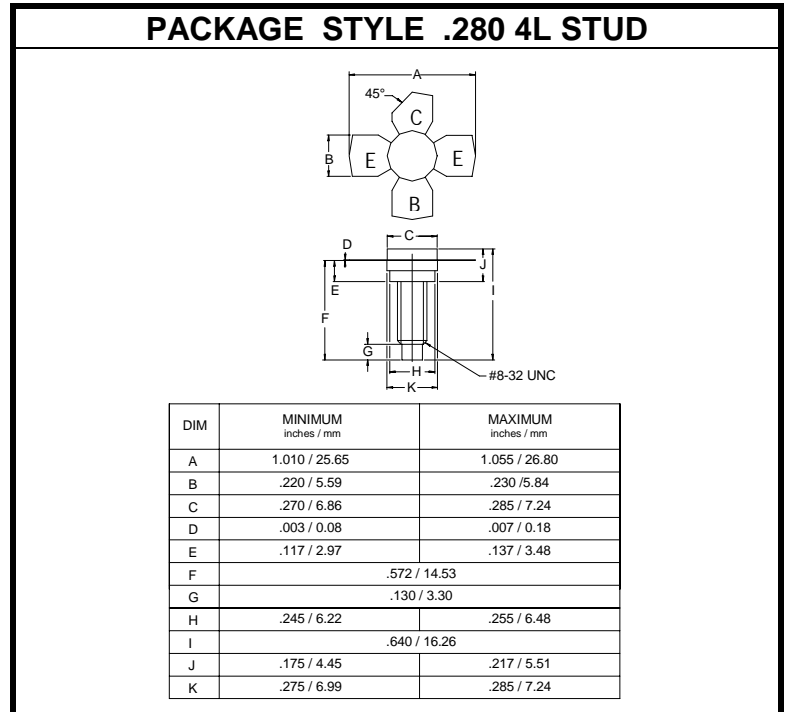
The **ASI BLX92A** is Designed for transmitting applications in class-A, B or C with a supply voltage up to 28 V

FEATURES:

- High Gain - 11.0 dB Min.
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	0.7 A
V_{CB}	65 V
P_{DISS}	6.0 W @ T _C = 25 °C
T_J	-65 to +200 °C
T_{STG}	-65 to +150 °C
θ_{JC}	9.8 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 10 mA	65			V
BV_{CES}	I _C = 10 mA	65			V
BV_{CEO}	I _C = 25 mA	33			V
BV_{EBO}	I _E = 1.0 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	10			---
f_T	V _{CE} = 5.0 V I _C = 100 mA		1.2		GHz
C_c	V _{CB} = 10 V f = 1.0 MHz		6.5		pF
C_e	V _{EB} = 0 V f = 1.0 MHz		25		pF
P_G η_C	V _{CE} = 28 V P _{OUT} = 2.5 W f = 470 MHz	11 60			dB %